Supporting Information

Stabilizing V$_2$O$_3$ in carbon nanofiber flexible films for ultrastable potassium storage

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Content

Experiment

Material Synthesis: All chemicals used in the experiment are analytical grade and were from Macklin without any further purification. The flexible films, V_2O_3/CNF, were prepared by electrospinning method within thermal calcination. The vanadyl acetylacetonate ($V(acac)_3$, 0.2786 g) was first dissolved in DMF to obtain a clear solution. Next, polyacrylonitrile (PAN, FW=150000) was added and continuously stirred overnight at room temperature to form the homogenous solution. Then, an electrospinning process was carried out with the voltage of 30 KV and a distance of 18 cm. Finally, the obtained film was calcined in N_2 atmosphere at 800 °C for 2 h with 10 °C/min. The final product was recorded as vanadium-oxide/carbon nanofibers (V_2O_3/CNF). The contrastive sample, carbon nanofibers (C), was prepared by the same method with only PAN. And the vanadium-oxide (V_2O_3) was prepared through the $V(acac)_3$ powder with the same calcination conditions.

Material Characterization: XRD measurements were performed using X-ray powder diffraction (XRD, Rigaku Co, Japan, D/MAX-γA) with Cu Kα radiation (λ=1.54056 Å) at a scan rate of 8 ° min^{-1}. The morphologies were systematically characterized by scanning electron microscopy (SEM, JEOL JSM-6700 M) and transmission electron microscopy (TEM, Hitachi H-800) coupled with energy dispersive X-ray (EDX) analysis. TGA was performed on TGA-5500 in the air from room temperature to 850 °C with a temperature ramp of 10 °C min^{-1}. The XPS was performed using (XPS, ESCALAB 250). Raman spectra were tested using Confocal Laser MicroRaman Spectrometer (Via-Reflex/inVia-Reflex).

Electrochemical Measurements: The electrochemical properties were evaluated with coin-type cells assembled in an argon-filled glove box (O_2 and H_2O < 0.1 ppm). The V_2O_3/CNF flexible films were directly used as working electrode with a loading about 1.15 mg cm^{-2} and the 0.636 cm^2 of average area. The half cells with 2032 coin-type were assembled using potassium as counter electrode and glass fiber as separator. The electrolyte was 3 M KFSI dissolved in a mixed solution of ethylene carbonate/propylene carbonate (EC/DEC, 1:1 by volume). Galvanostatic charge/discharge tests were carried out on the Neware CT3008W in the voltage range of 0.01−3.0 V. And the electrochemical performance of V_2O_3@CNF electrode was based the total mass of V_2O_3@CNF. Electrochemical impedance spectroscopy (EIS) and Cyclic voltammetry (CV) test were conducted on CHI760E electrochemical workstation. The CV tests were carried out in the potential range of 0.01−3.0 V at different scanning rate.

DFT calculation: All calculations were performed using the plane-wave periodic density functional method (DFT) in the Vienna *ab initio* simulation package (VASP) [1,2]. The electron ion interaction was described with the projector augmented wave (PAW) method [3,4]. The electron exchange and correlation energy were treated within the generalized gradient approximation (GGA) in the form of the Perdew-Burke-Ernzerhof (PBE) functional [5]. The cut-off energy was set up to 500 eV. The force convergence was set to be lower than 0.02 eV/Å, and the total energy convergence was set to be smaller than 10^{-5} eV. Electron smearing of $\sigma = 0.05$ eV was used following the the Gaussian scheme.

The Brillouin zone was sampled using Monkhorst–Pack scheme with a k-point mesh of $3 \times 3 \times 1$ centered at the Γ-centered point for the structural relaxation, and $3 \times 3 \times 1$ k-point mesh was used for the static calculations of charge density difference and Bader charge, $9 \times 9 \times 1$ k-point mesh was used for the static calculations of density of states [6]. The structure relaxation was continued until the forces on all the atoms are converged to less than 0.02 eV/Å.

The crystal data of the initial structure comes from the Crystallographic database following article [7]. The optimized lattice constants of graphene and V_2O_3 are 2.52 and a=c=5.12 Å, c= 13.87 Å, where the value of c/a was 2.70. The U parameter was set at 2.68 for V d-electrons [8]. Spin polarized calculations (collinear) were performed (ISPIN=2). Taking into account the paramagnetic characteristics of vanadium oxide where the magnetic moment of vanadium atoms was set to 2μB and the others to 0μB [9,10]. Zero damping DFT-D3 method of Grimme.

The slab model of the most stable V_2O_3 (0001) surface contains nine atomic layers in thickness with 3 bottom layers fixed while relaxing other atoms besides, and a 2×2 supercell in the lateral plane is adopted. Graphene with a 4×4 supercell. The lattice mismatch is about 1.35%. The vacuum slab was set up to 12 Å.

Considering previous studies on vanadium oxide and the actual preparation conditions and terminations, a (0001) surface with a pure-oxygen exposure terminations and a few V=O terminations were used [11-14].
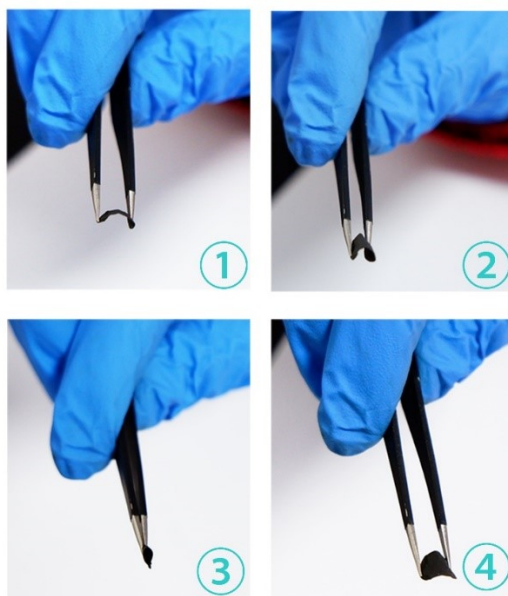
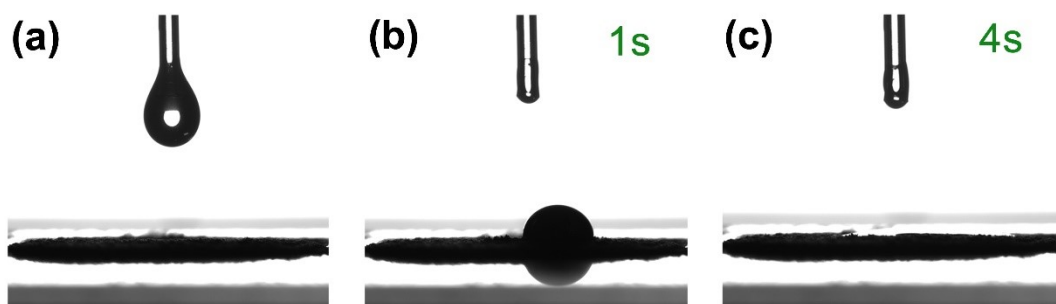**Figure S1.** Flexibility of the V$_2$O$_3$/CNF film.

Figure S2. (a), (b), (c) Wettability of the C with electrolyte. C electrode materials cannot be quickly and completely infiltrated by electrolyte.

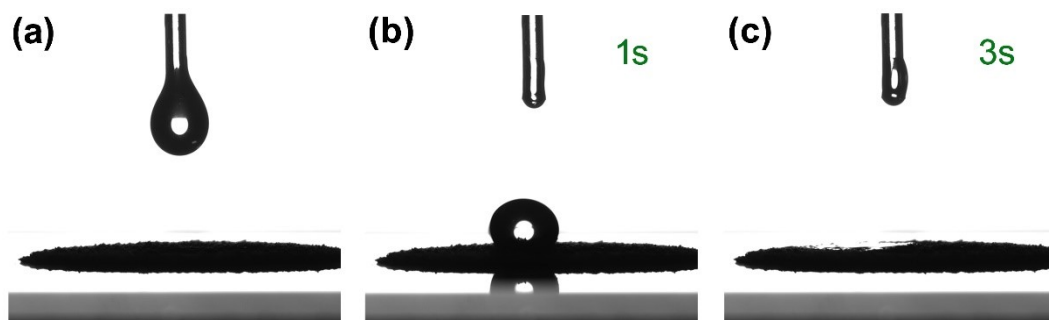**Figure S3** (a), (b), (c) Wettability of the V_2O_3 with electrolyte. V_2O_3 electrode materials cannot be quickly and completely infiltrated by electrolyte.

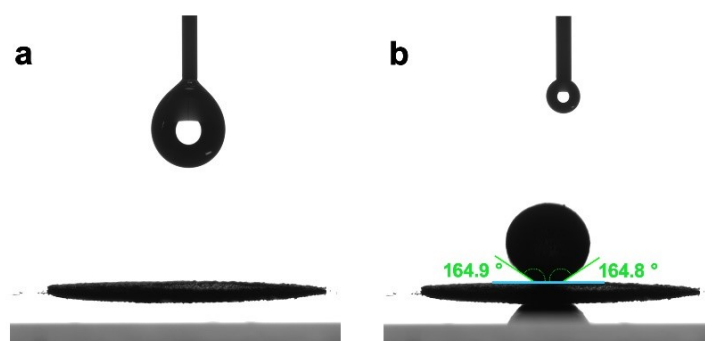**Figure S4.** (a), (b) Wettability of the C with H_2O.
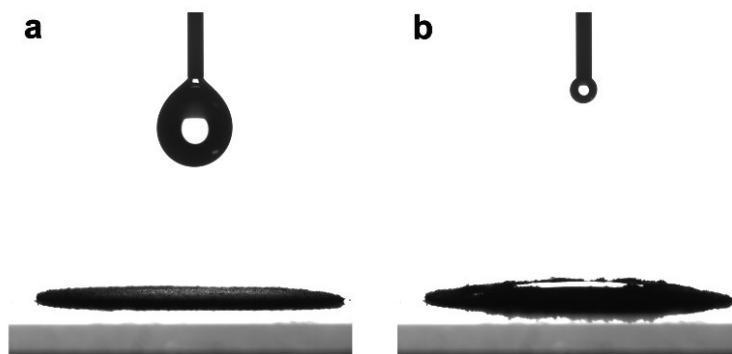
Figure S5. (a), (b) Wettability of the V_2O_3 with H_2O.
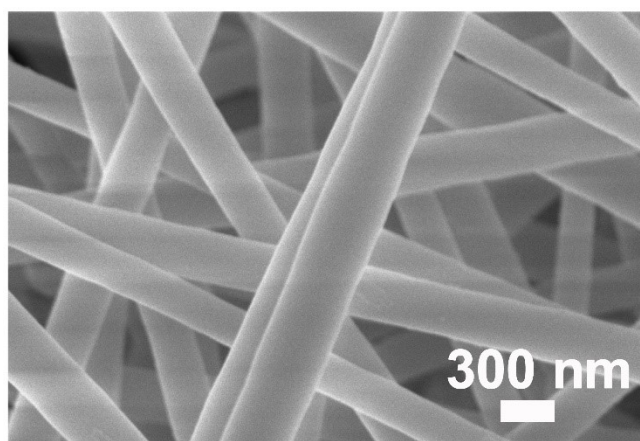
Figure S6. SEM image for the precursor film of V_2O_3/CNF.
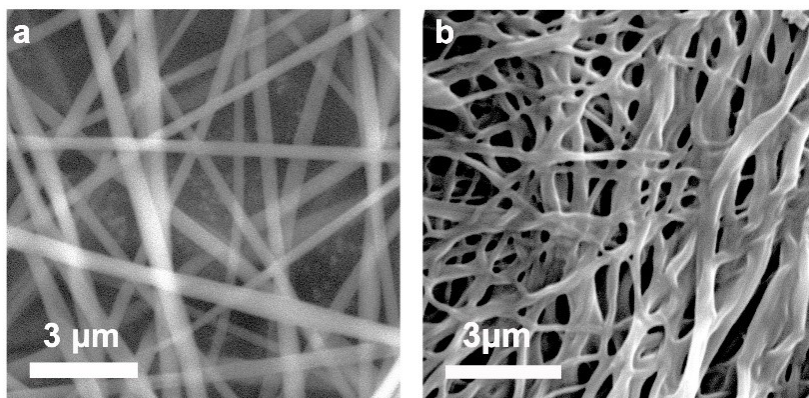
Figure S7. SEM image for the a) precursor film of C and b) C.
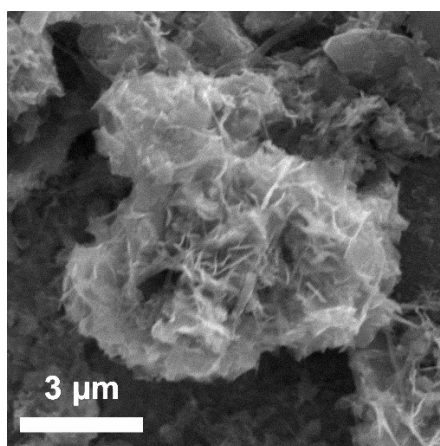
Figure S8. SEM image for the V_2O_3.
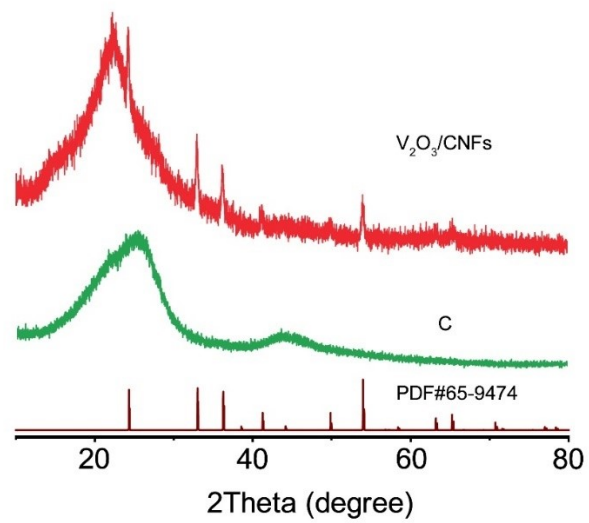
Figure S9. XRD pattern of V_2O_3/CNF and C.
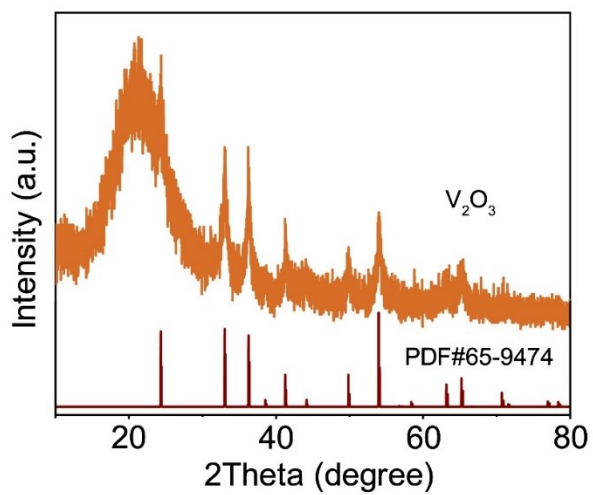
Figure S10. XRD pattern of V_2O_3.
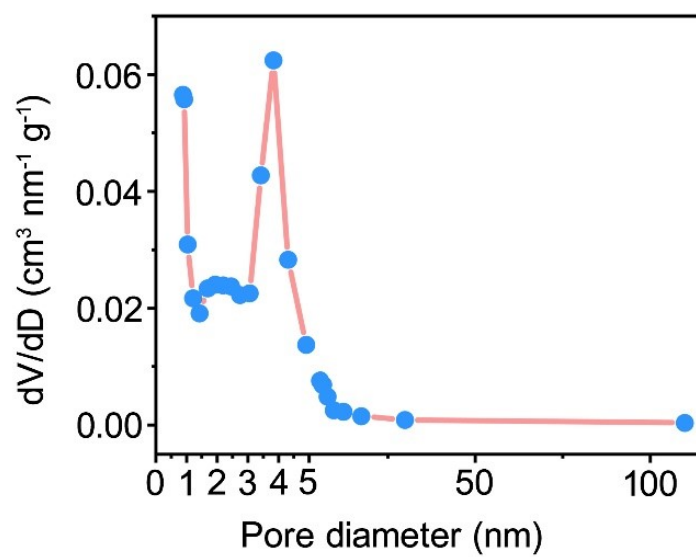
Figure S11. Pore distributions curves of V_2O_3/CNF.
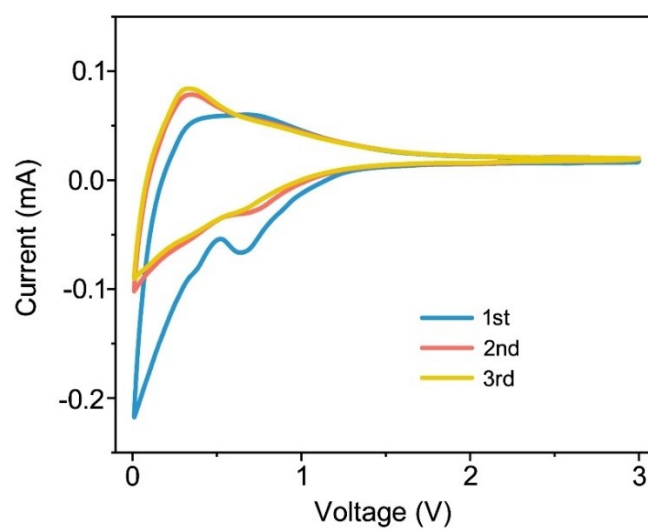
Figure S12. CV curves of C electrode.
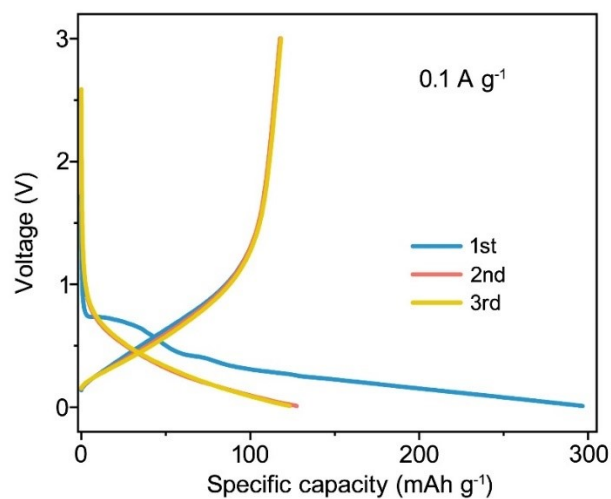
Figure S13. Charge-discharge profiles of C electrode at 0.1 A g^{-1} for initial three cycles.
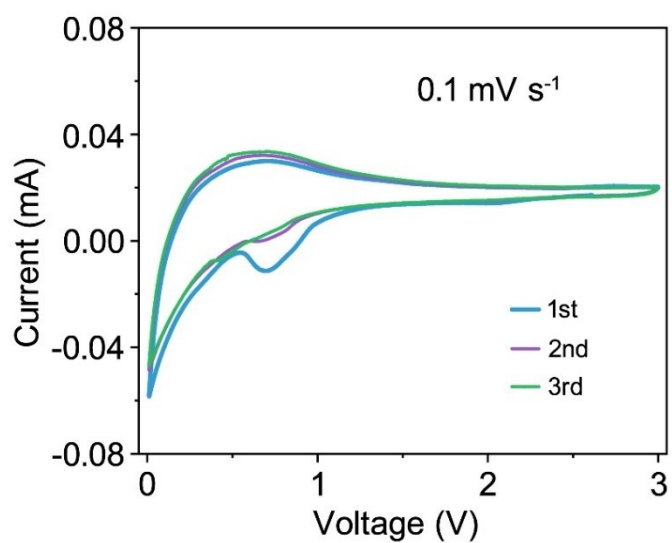
Figure S14. CV curves of V$_2$O$_3$ electrode.
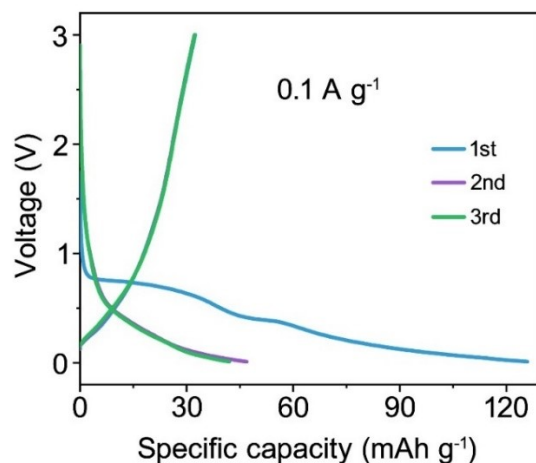
Figure S15. Charge-discharge profiles of V_2O_3 electrode at 0.1 A g^{-1} for initial three cycles.
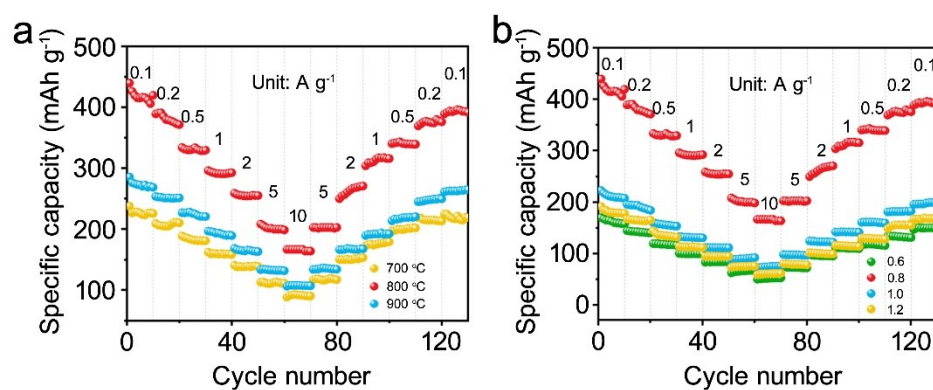
Figure S16. (a) Rate performance of V_2O_3/CNF at different calcination temperature; (b) Rate performance of V_2O_3/CNF with different content of raw material vanadium.

From Figure S16a, the samples at 800 °C had the best performance, so 800 °C was the best temperature for the formation of the samples. And from Figure S16b, the materials prepared with 0.8 mmol had the best electrochemical properties. Thus, the 800 °C with the initial raw material of 0.8 mmol are the the best synthesis condition for the V_2O_3/CNF.
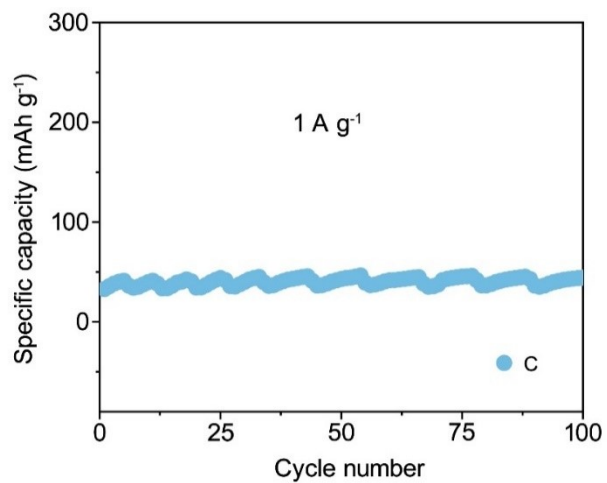
Figure S17. Cycle life of C electrode at 1 A g^{-1}.
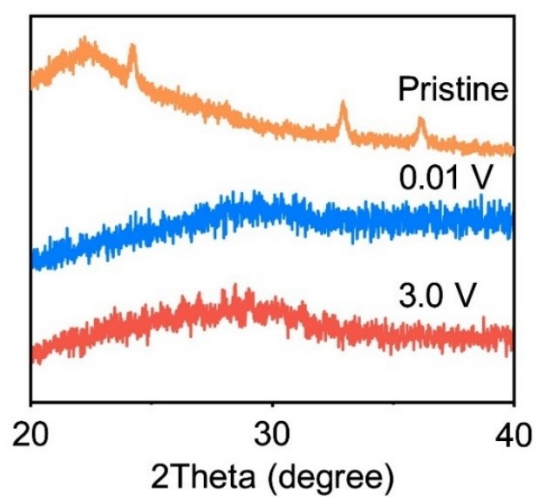
Figure S18. Ex-situ XRD patterns of V$_2$O$_3$/CNF at the first cycle.
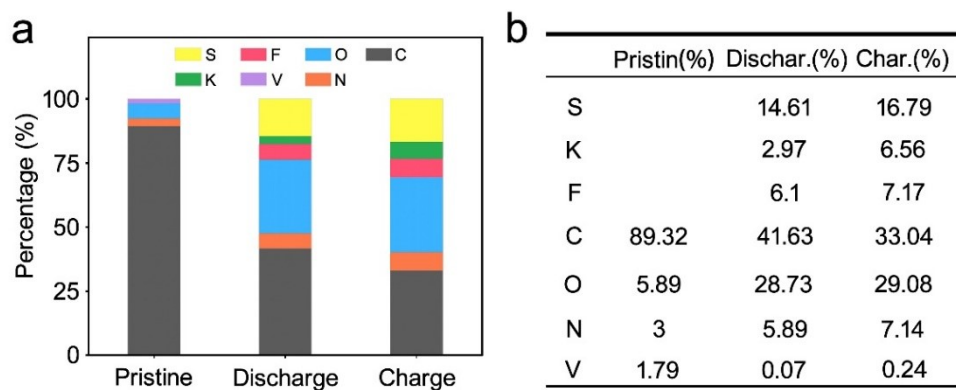
Figure S19. (a), (b) Element content information of V_2O_3/CNF at different state.

	Pristin(%)	Dischar.(%)	Char.(%)
S		14.61	16.79
K		2.97	6.56
F		6.1	7.17
C	89.32	41.63	33.04
O	5.89	28.73	29.08
N	3	5.89	7.14
V	1.79	0.07	0.24
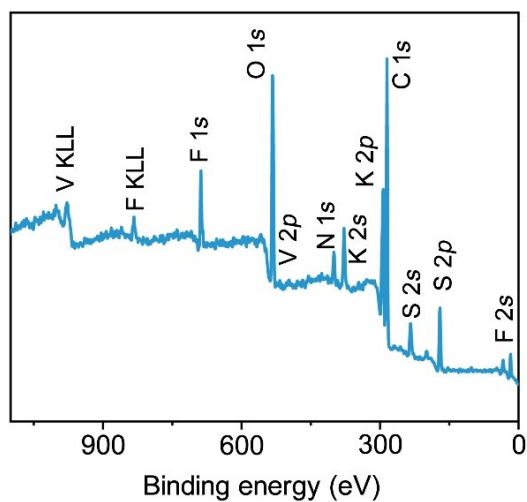
Figure S20. XPS of discharged V_2O_3/CNF.
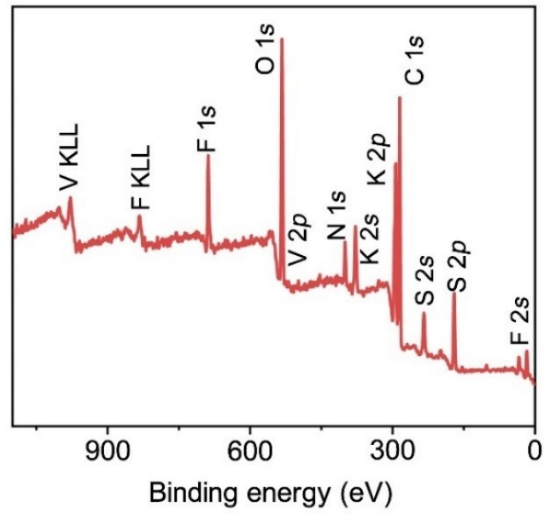
Figure S21. XPS of charged V_2O_3/CNF.
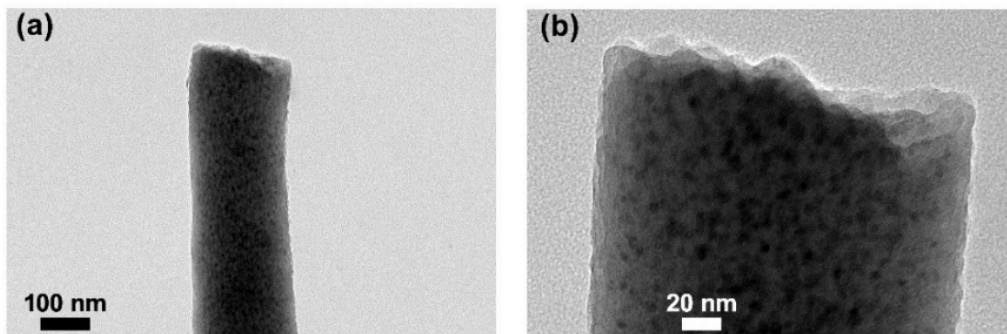
Figure S22. Partially enlarged TEM images of V_2O_3/CNF film after rate cycles.
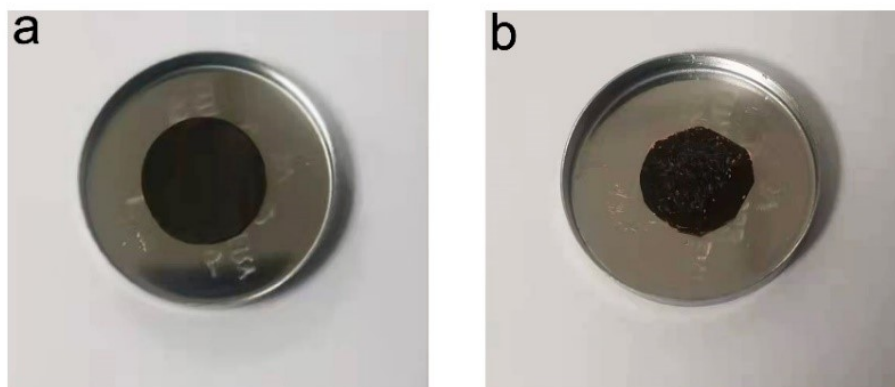
Figure S23. (a) Photo of V_2O_3@CNF electrode at pristine, (b) Photo of V_2O_3@CNF electrodes after cycling.
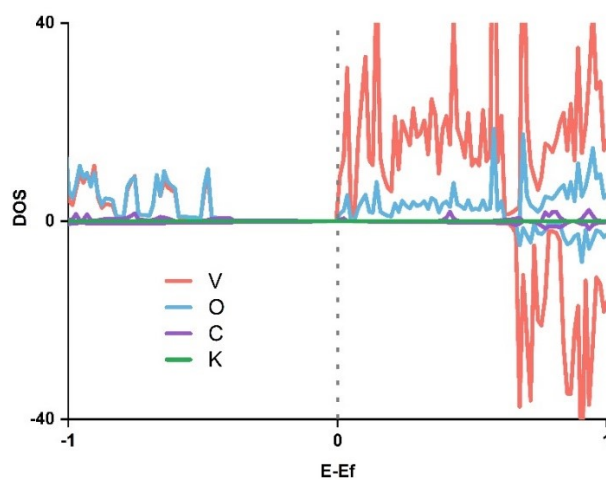
Figure S24. Local Density-of-States of each element for the V_2O_3/C without C-O-V bond.

Table S1. Electrochemical performance of different anode materials on potassium ion battery

Materials	Rate capacity (mAh g^{-1})	Cycle life	reference
carbons	133 at 5 A g^{-1}	the retention of 81% at 1 A g^{-1} over 400 cycles	**15**
flower like-NiS$_2$	190 at 2 A g^{-1}	239 mAh g^{-1} after 500 cycles at 1 A g^{-1}	**16**
CuP$_2$/Cu nanowire	101 at 10 A g^{-1},	392 mAh g^{-1} with retention of 99.5% after 50 cycles at 0.1 A g^{-1}	**17**
MnCo$_2$O$_4$	152 at 1A g^{-1}	126 mAh g^{-1} over 200 cycles at 0.1A g^{-1}	**18**
Co$_3$O$_4$@N−C	80 at 2 C	213 mAh g^{-1} after 740 cycles at 0.5 A g^{-1},	**19**

Bi@N-CNCs	235.5 at 10 A g^{-1},	327.5 mAh g^{-1} after 300 cycles at 1 A g^{-1}; 224 mAh g^{-1} with retention of 95.3% at 5 A g^{-1} over 1200 cycles	[20]
Co$_3$Se$_4$ QD	154 at 5 A g^{-1},	407 mAh g^{-1} after 550 cycles at 0.1 A g^{-1}; 200 mAh g^{-1} at 1 A g^{-1} after 10000 cycles	[21]
Bi$_2$MoO$_6$	165.3 at 0.5 A g^{-1}	121.7 mAh g^{-1} after 600 cycles at 0.1 A g^{-1}	[22]
CuS$_2$@NC	257 at 6 A g^{-1}	317 mAh g^{-1} after 1200 cycles at 1 A g^{-1}	[23]
soft carbon	115 at 5.0 A g^{-1}	the retention of 92.4% at 1.0 A g^{-1} after 1000 cycles	[24]
Cu$_3$P	-	174 mA h g^{-1} at 1 A g^{-1} after 300 cycles	[25]
BiSb@TCS	119.3 at 6 A g^{-1}	181 mAh g^{-1} after 5700 cycles at 2 A g^{-1},	[26]

V_2O_3@C	116.6 at 5 A g^{-1}	147.9 mAh g^{-1} after 1800 cycles at 2 A g^{-1}	**27**
VO/C	104 at 15 A g^{-1}	345 mAh g^{-1} at 0.1 A g^{-1} after 400 cycles; 241 mAh g^{-1} at 1 A g^{-1} over 1000 cycles	**28**
V_2O_3/CNF	175 at 10 A g^{-1}	380 mAh g^{-1} after 500 cycles at 0.1 A g^{-1}; the retention of 98% after 2500 cycles at 1 A g^{-1}	**This work**

Table S2. Coulombic efficiency of the V_2O_3/CNF in initial five cycles.

Cycle number	Coulombic efficiency (%)
1	27.9
2	86.7
3	95.6
4	98.4
5	99.2

Table S3. Bader charge analysis of V_2O_3/CNF film with C-O-V bond

No. /Element	V	O	C	K
Sun	53.50	255.11	123.26	8.13
Gains and Losses	-14.50	40.89	-0.74	-0.87

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